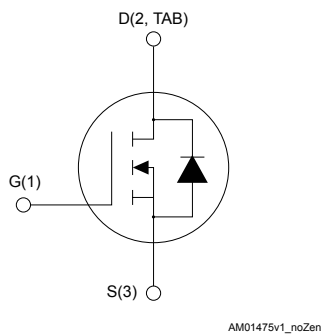
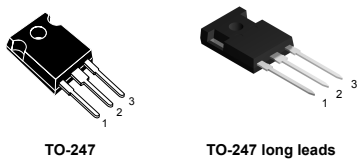


N-channel 950 V, 120 mΩ typ., 38 A, MDmesh DK5 Power MOSFETs in TO-247 and TO-247 long leads packages



Features

Order code	V _{DS}	R _{DS(on)} max.	I _D
STW40N95DK5	950 V	130 mΩ	38 A
STWA40N95DK5			

- Fast-recovery body diode
- Best R_{DS(on)} x area
- Low gate charge, input capacitance and resistance
- 100% avalanche tested
- Extremely high dv/dt ruggedness

Applications

- Switching applications

Description

These very high voltage N-channel Power MOSFETs are part of the MDmesh DK5 fast-recovery diode series. The MDmesh DK5 combines very low recovery charge (Q_{rr}) and recovery time (t_{rr}) with an excellent improvement in R_{DS(on)} * area and one of the most effective switching behaviors, ideal for half bridge and full bridge converters.



Product status links

[STW40N95DK5](#)

[STWA40N95DK5](#)

Product summary

Order code	STW40N95DK5
Marking	40N95DK5
Package	TO-247
Packing	Tube
Order code	STWA40N95DK5
Marking	40N95DK5
Package	TO-247 long leads
Packing	Tube

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 30	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^{\circ}\text{C}$	38	A
	Drain current (continuous) at $T_C = 100\text{ }^{\circ}\text{C}$	24	
$I_{DM}^{(1)}$	Drain current (pulsed)	152	A
P_{TOT}	Total power dissipation at $T_C = 25\text{ }^{\circ}\text{C}$	450	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	50	V/ns
$dv/dt^{(3)}$	MOSFET dv/dt ruggedness	50	V/ns
T_{stg}	Storage temperature range	-55 to 150	$^{\circ}\text{C}$
T_J	Operating junction temperature range		$^{\circ}\text{C}$

1. Pulse width limited by safe operating area.
2. $I_{SD} \leq 38\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$, $V_{DS}(\text{peak}) \leq V_{(BR)DSS}$, $V_{DD} = 760\text{ V}$.
3. $V_{DS} \leq 760\text{ V}$.

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance, junction-to-case	0.28	$^{\circ}\text{C}/\text{W}$
R_{thJA}	Thermal resistance, junction-to-ambient	50	$^{\circ}\text{C}/\text{W}$

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Maximum current during repetitive or single pulse avalanche	13	A
E_{AS}	Single pulse avalanche energy (starting $T_J = 25\text{ }^{\circ}\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	730	mJ

2 Electrical characteristics

$T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$, $V_{GS} = 0\text{ V}$	950			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$, $V_{DS} = 950\text{ V}$			1	μA
		$V_{GS} = 0\text{ V}$, $V_{DS} = 950\text{ V}$, $T_C = 125\text{ }^{\circ}\text{C}^{(1)}$			100	μA
I_{GSS}	Gate-source leakage current	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 20\text{ V}$			± 10	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DD} = V_{GS}$, $I_D = 100\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 19\text{ A}$		120	130	m Ω

1. Defined by design, not subject to production test.

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0\text{ V}$	-	3480	-	pF
C_{oss}	Output capacitance		-	235	-	pF
C_{rss}	Reverse transfer capacitance		-	2.3	-	pF
$C_{o(tr)}^{(1)}$	Equivalent capacitance time related	$V_{GS} = 0\text{ V}$, $V_{DS} = 0\text{ to }760\text{ V}$	-	371	-	pF
$C_{o(er)}^{(2)}$	Equivalent capacitance energy related		-	134	-	pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz}$, $I_D = 0\text{ A}$	-	2	-	Ω
Q_g	Total gate charge	$V_{DD} = 760\text{ V}$, $I_D = 38\text{ A}$, $V_{GS} = 0\text{ to }10\text{ V}$ (see Figure 14. Test circuit for gate charge behavior)	-	100	-	nC
Q_{gs}	Gate source charge		-	19.5	-	nC
Q_{gd}	Gate drain charge		-	67.6	-	nC

1. $C_{o(tr)}$ is a constant capacitance value that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

2. $C_{o(er)}$ is a constant capacitance value that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DS} = 475\text{ V}$, $I_D = 19\text{ A}$, $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$	-	30	-	ns
t_r	Rise time		-	15	-	ns
$t_{d(off)}$	Turn-off delay time	(see Figure 13. Test circuit for resistive load switching times and Figure 18. Switching time waveform)	-	82	-	ns
t_f	Fall time		-	11	-	ns

Table 7. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		38	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		152	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 38\text{ A}$, $V_{GS} = 0\text{ V}$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 19\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$ (see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	170		ns
Q_{rr}	Reverse recovery charge		-	1.4		μC
I_{RRM}	Reverse recovery current		-	15		A
t_{rr}	Reverse recovery time	$I_{SD} = 19\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$, $T_J = 150\text{ }^\circ\text{C}$ (see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	340		ns
Q_{rr}	Reverse recovery charge		-	5		μC
I_{RRM}	Reverse recovery current		-	30		A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%.

2.1 Electrical characteristics (curves)

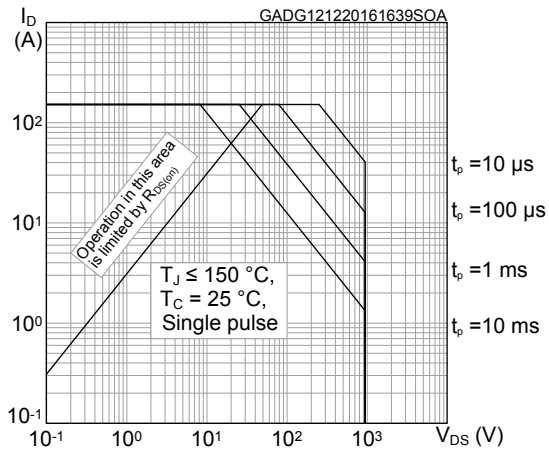
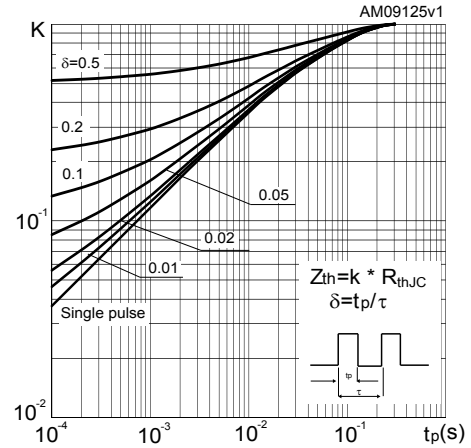
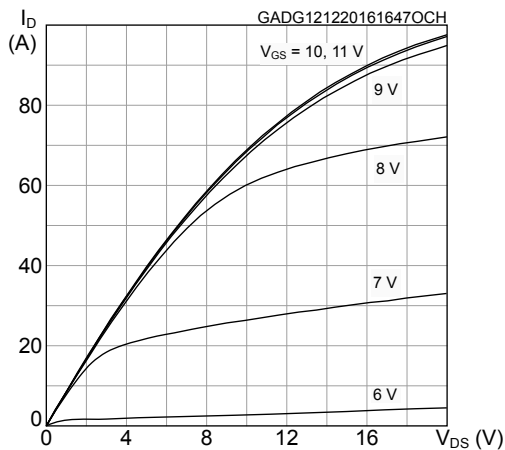
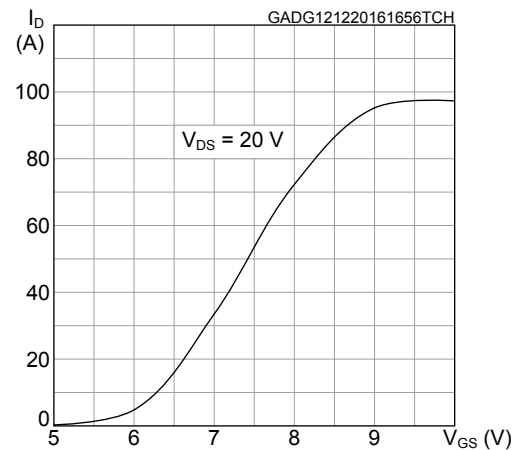
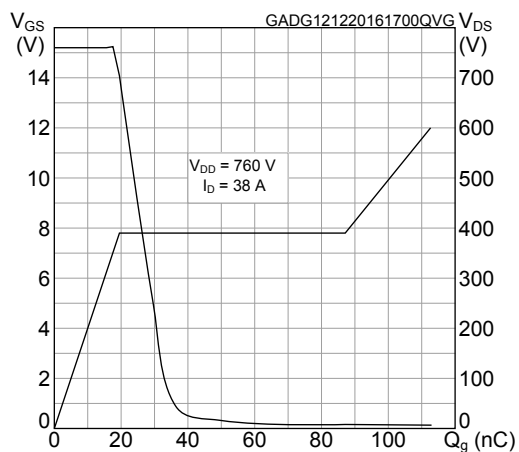
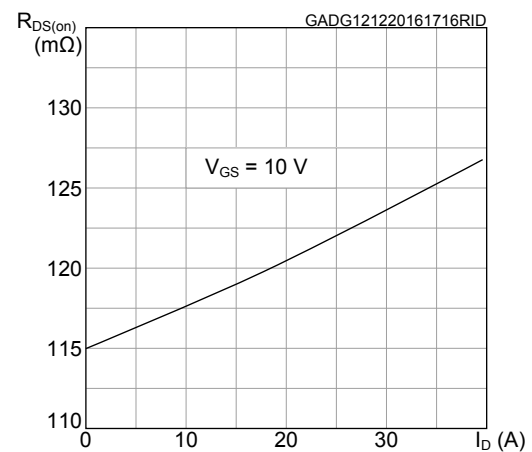
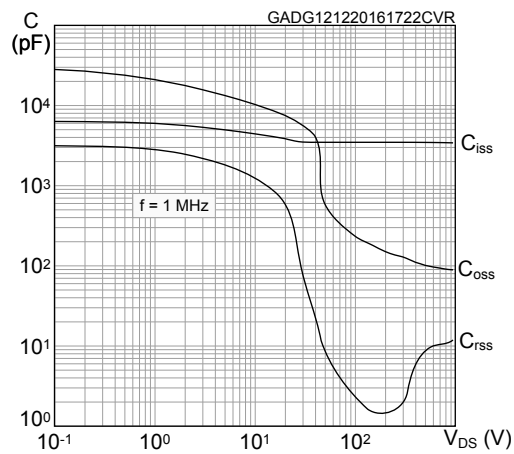
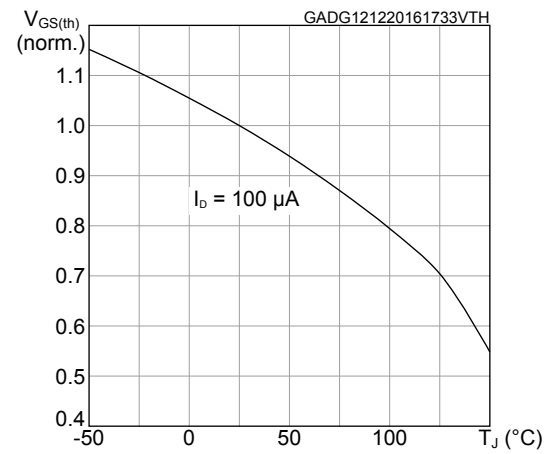
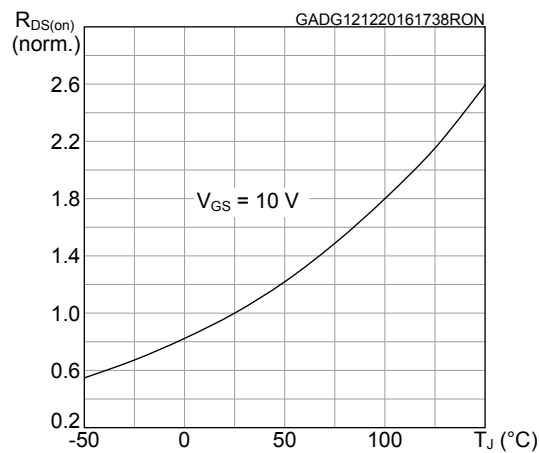
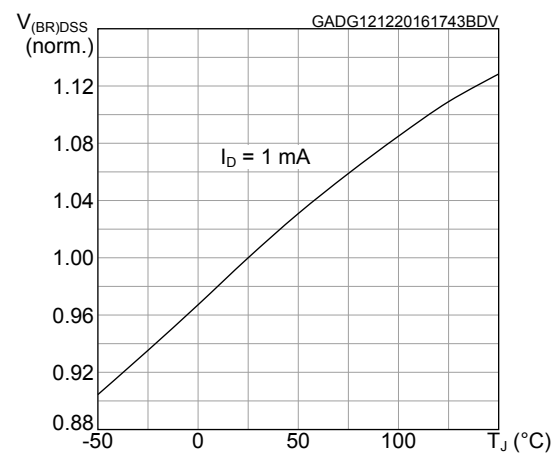
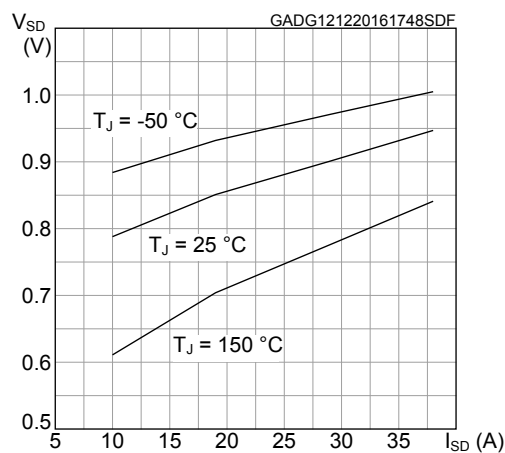
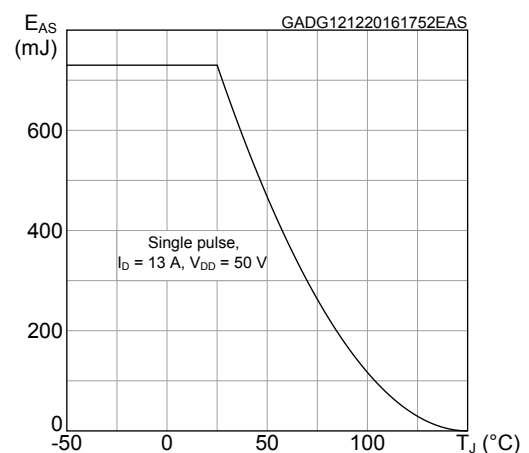
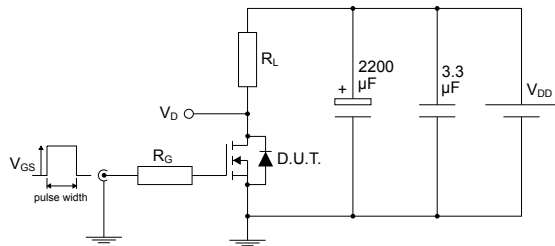
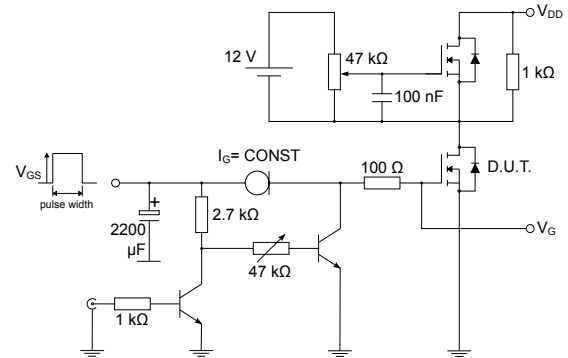
Figure 1. Forward bias safe operating area

Figure 2. Thermal impedance

Figure 3. Output characteristics

Figure 4. Transfer characteristics

Figure 5. Gate charge vs gate-source voltage

Figure 6. Static drain-source on-resistance


Figure 7. Capacitance variations

Figure 8. Normalized gate threshold voltage vs temperature

Figure 9. Normalized on-resistance vs temperature

Figure 10. Normalized $V_{(BR)DSS}$ vs temperature

Figure 11. Source-drain diode forward characteristics

Figure 12. Maximum avalanche energy vs starting T_J


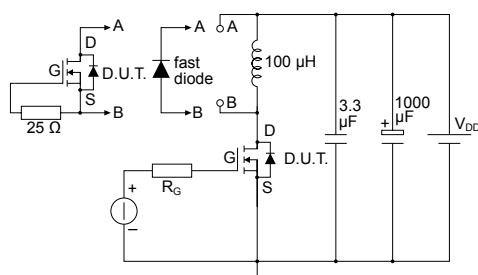
3 Test circuits

Figure 13. Test circuit for resistive load switching times


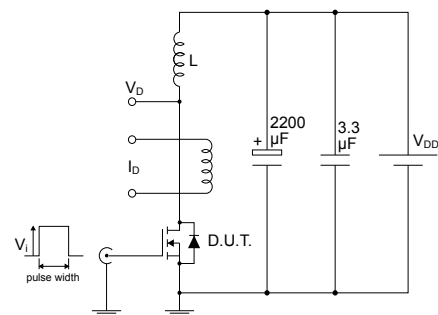
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Figure 14. Test circuit for gate charge behavior


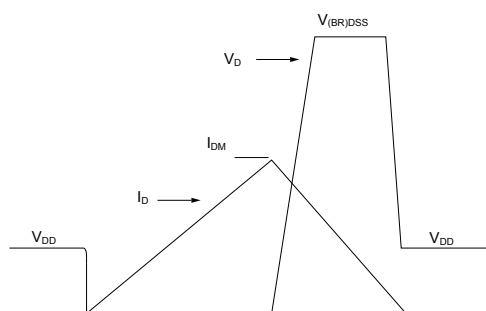
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Figure 15. Test circuit for inductive load switching and diode recovery times


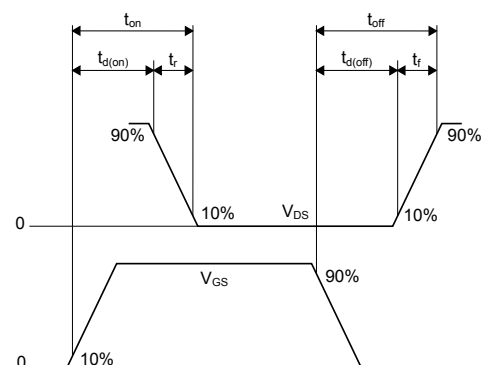
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Figure 16. Unclamped inductive load test circuit


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Figure 17. Unclamped inductive waveform


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Figure 18. Switching time waveform


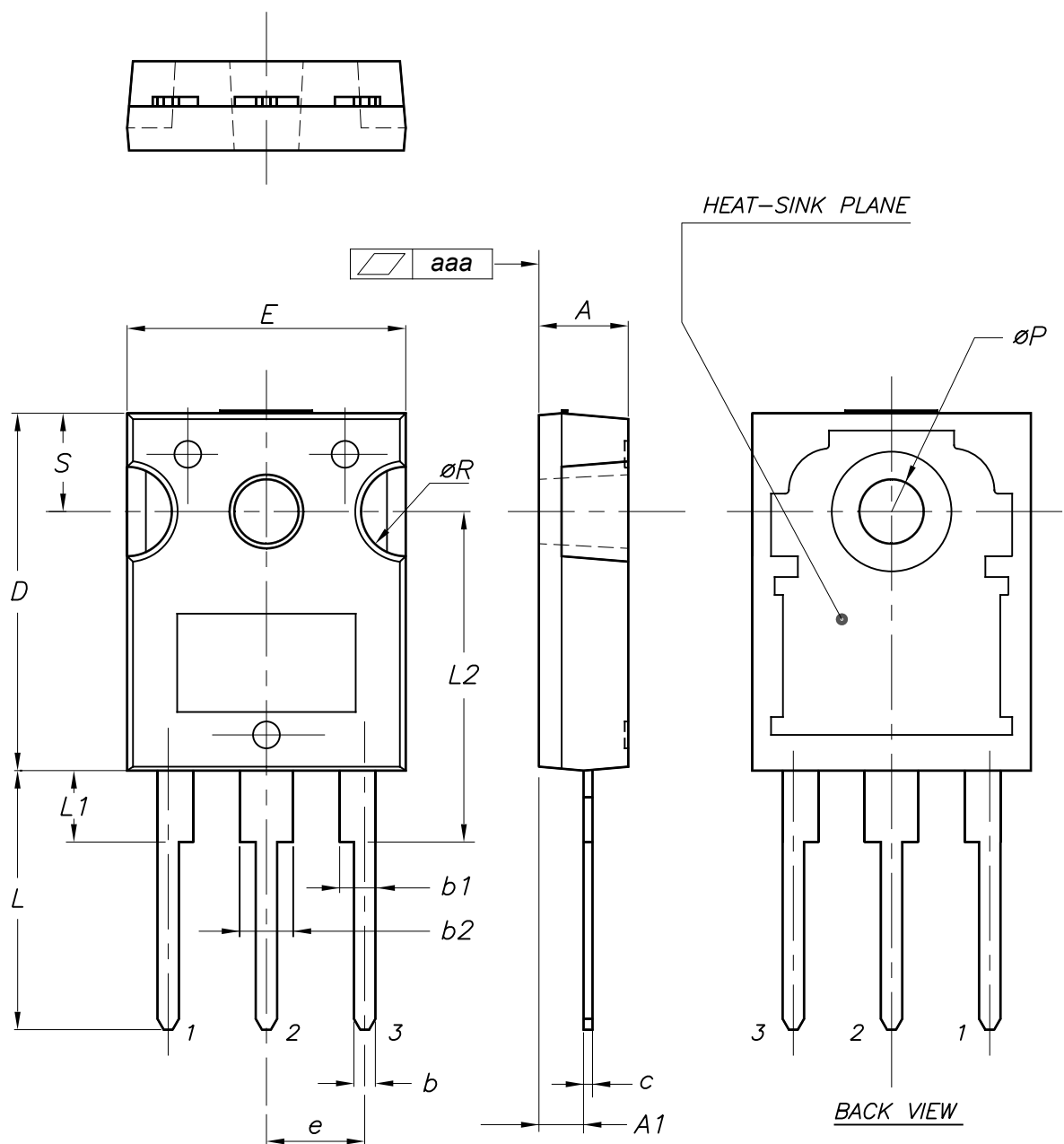
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4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 TO-247 package information

Figure 19. TO-247 package outline



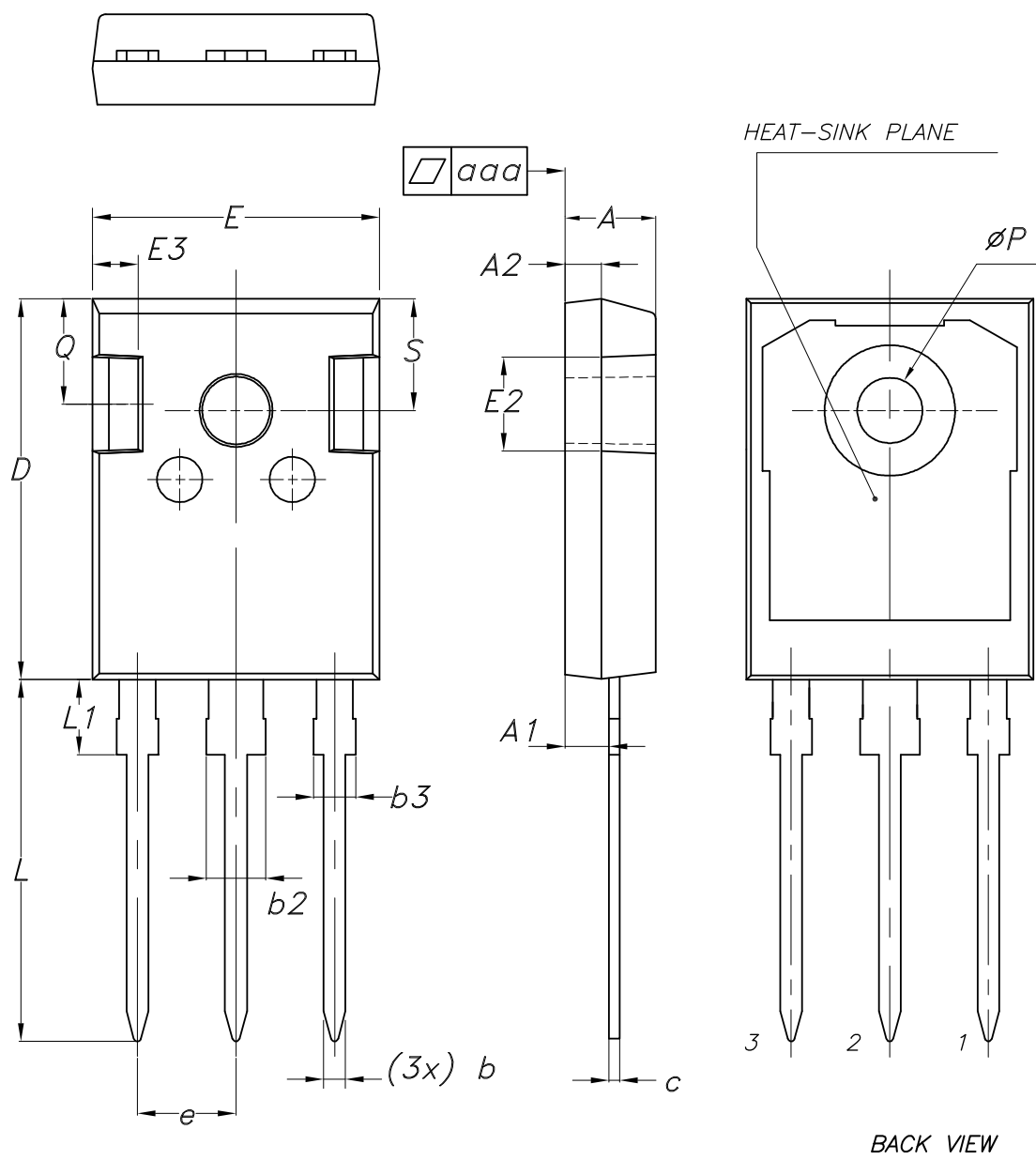
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Table 8. TO-247 package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70
aaa		0.04	0.10

4.2 TO-247 long leads package information

Figure 20. TO-247 long leads package outline



8463846_3

Table 9. TO-247 long leads package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.90	5.00	5.10
A1	2.31	2.41	2.51
A2	1.90	2.00	2.10
b	1.16		1.26
b2			3.25
b3			2.25
c	0.59		0.66
D	20.90	21.00	21.10
E	15.70	15.80	15.90
E2	4.90	5.00	5.10
E3	2.40	2.50	2.60
e	5.34	5.44	5.54
L	19.80	19.92	20.10
L1			4.30
P	3.50	3.60	3.70
Q	5.60		6.00
S	6.05	6.15	6.25
aaa		0.04	0.10

Revision history

Table 10. Document revision history

Date	Revision	Changes
19-Sep-2013	1	First release.
13-Nov-2015	2	Updated title, features and description in cover page. Updated Section 10 : "Electrical characteristics" and Section 12.1:"TO-247 package information" Minor text changes.
12-Apr-2016	3	Updated title,silhouette and description in cover page. Updated <i>Table 2: "Absolute maximum ratings"</i> . Updated <i>Section 10: "Electrical characteristics"</i> . Added <i>Figure 21: "TO-247 long lead package outline"</i> . Minor text changes
12-Dec-2016	4	Datasheet status promoted from preliminary to production data. Updated document title on cover page. Updated <i>Table 2: "Absolute maximum ratings"</i> , <i>Table 4: "Thermal data"</i> , <i>Table 5: "On/off states"</i> , <i>Table 6: "Dynamic"</i> and <i>Table 8: "Source-drain diode"</i> . Added <i>Section 2.1: "Electrical characteristics (curves)"</i> . Minor text changes
11-Aug-2021	5	Updated Table 1. Absolute maximum ratings . Updated Section 4 Package information . Minor text changes.

Contents

1	Electrical ratings	2
2	Electrical characteristics	3
2.1	Electrical characteristics (curves)	5
3	Test circuits	7
4	Package information	8
4.1	TO-247 package information	8
4.2	TO-247 long leads package information	10
	Revision history	12

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